PowerMOS transistor Logic level TOPFET

BUK101-50DL

DESCRIPTION

Monolithic temperature and overload protected logic level power MOSFET in a 3 pin plastic envelope, intended as a general purpose switch for automotive systems and other applications.

APPLICATIONS

General controller for driving
- lamps
- motors
- solenoids
- heaters

FEATURES

- Vertical power DMOS output stage
- Low on-state resistance
- Overload protection against over temperature
- Overload protection against short circuit load
- Latched overload protection reset by input
- 5 V logic compatible input level
- Control of power MOSFET and supply of overload protection circuits derived from input
- Lower operating input current permits direct drive by micro-controller
- ESD protection on input pin
- Overvoltage clamping for turn off of inductive loads

QUICK REFERENCE DATA

SYMBOL	PARAMETER		MAX.	UNIT
V_{DS}	Continuous drain source voltage		50	V
I_D	Continuous drain current		26	A
P_D	Total power dissipation		75	W
T_j	Continuous junction temperature		150	˚C
$R_{DS(ON)}$	Drain-source on-state resistance		60	mΩ
I_{ISL}	Input supply current	V_{IS} = 5 V	650	µA

FUNCTIONAL BLOCK DIAGRAM

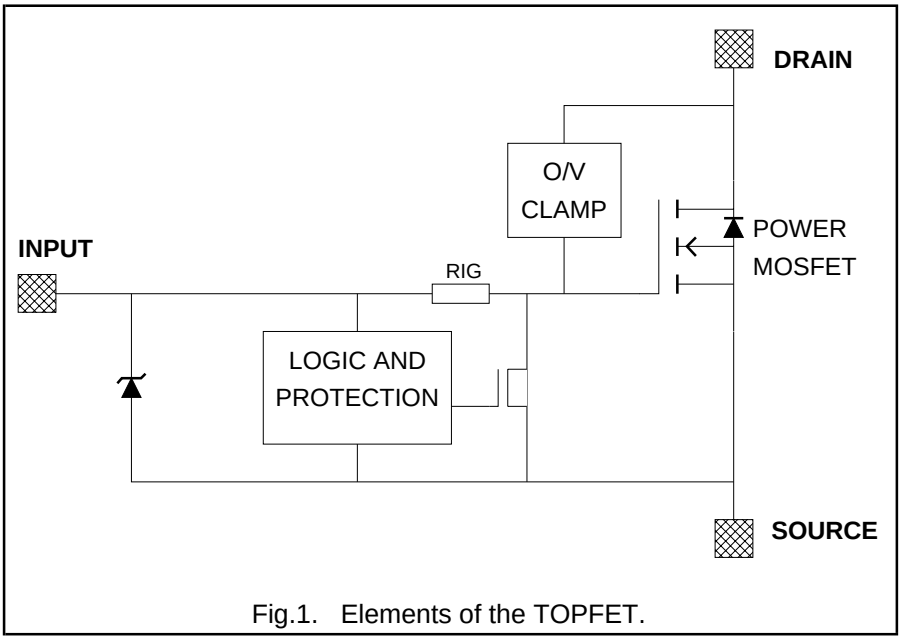
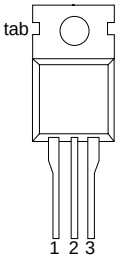


Fig.1. Elements of the TOPFET.

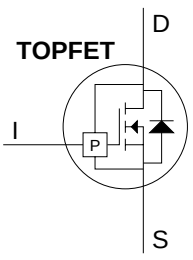
PINNING - TO220AB

PIN	DESCRIPTION
1	input
2	drain
3	source
tab	drain

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Continuous drain source voltage[1]	-	-	50	V
V_{IS}	Continuous input voltage	-	0	6	V
I_D	Continuous drain current	$T_{mb} \leq 25$ ˚C; V_{IS} = 5 V	-	26	A
I_D	Continuous drain current	$T_{mb} \leq 100$ ˚C; V_{IS} = 5 V	-	16	A
I_{DRM}	Repetitive peak on-state drain current	$T_{mb} \leq 25$ ˚C; V_{IS} = 5 V	-	100	A
P_D	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	75	W
T_{stg}	Storage temperature	-	-55	150	˚C
T_j	Continuous junction temperature[2]	normal operation	-	150	˚C
T_{sold}	Lead temperature	during soldering	-	250	˚C

OVERLOAD PROTECTION LIMITING VALUES

With the protection supply provided via the input pin, TOPFET can protect itself from two types of overload.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{ISP}	Protection supply voltage[3]	for valid protection	4	-	V
	Over temperature protection				
$V_{DDP(T)}$	Protected drain source supply voltage	V_{IS} = 5 V	-	50	V
	Short circuit load protection[4]				
$V_{DDP(P)}$	Protected drain source supply voltage[5]	V_{IS} = 5 V	-	20	V
P_{DSM}	Instantaneous overload dissipation	T_{mb} = 25 ˚C	-	1.3	kW

OVERVOLTAGE CLAMPING LIMITING VALUES

At a drain source voltage above 50 V the power MOSFET is actively turned on to clamp overvoltage transients.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{DROM}	Repetitive peak clamping current	V_{IS} = 0 V	-	26	A
E_{DSM}	Non-repetitive clamping energy	$T_{mb} \leq 25$ ˚C; I_{DM} = 26 A; $V_{DD} \leq 20$ V; inductive load	-	625	mJ
E_{DRM}	Repetitive clamping energy	$T_{mb} \leq 95$ ˚C; I_{DM} = 8 A; $V_{DD} \leq 20$ V; f = 250 Hz	-	40	mJ

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage	Human body model; C = 250 pF; R = 1.5 kΩ	-	2	kV

1 Prior to the onset of overvoltage clamping. For voltages above this value, safe operation is limited by the overvoltage clamping energy.

2 A higher T_j is allowed as an overload condition but at the threshold $T_{j(TO)}$ the over temperature trip operates to protect the switch.

3 The input voltage for which the overload protection circuits are functional.

4 For further information, refer to OVERLOAD PROTECTION CHARACTERISTICS.

5 The short circuit load protection is able to save the device providing the instantaneous on-state dissipation is less than the limiting value for P_{DSM}, which is always the case when V_{DS} is less than $V_{DDP(P)}$ maximum.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Thermal resistance					
$R_{th\ j\text{-}mb}$	Junction to mounting base	-	-	1.3	1.67	K/W
$R_{th\ j\text{-}a}$	Junction to ambient	in free air	-	60	-	K/W

STATIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(CL)DSS}$	Drain-source clamping voltage	V_{IS} = 0 V; I_D = 10 mA	50	-	-	V
$V_{(CL)DSS}$	Drain-source clamping voltage	V_{IS} = 0 V; I_{DM} = 2 A; $t_p \le 300$ µs; $\delta \le 0.01$	-	-	70	V
I_{DSS}	Zero input voltage drain current	V_{DS} = 12 V; V_{IS} = 0 V	-	0.5	10	µA
I_{DSS}	Zero input voltage drain current	V_{DS} = 50 V; V_{IS} = 0 V	-	1	20	µA
I_{DSS}	Zero input voltage drain current	V_{DS} = 40 V; V_{IS} = 0 V; T_j = 125 ˚C	-	10	100	µA
$R_{DS(ON)}$	Drain-source on-state resistance[1]	V_{IS} = 5 V; I_{DM} = 13 A; $t_p \le 300$ µs; $\delta \le 0.01$	-	45	60	mΩ

OVERLOAD PROTECTION CHARACTERISTICS

TOPFET switches off when one of the overload thresholds is reached. It remains latched off until reset by the input.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Short circuit load protection[2]	T_{mb} = 25 ˚C; L ≤ 10 µH; R_L = 10 mΩ				
$E_{DS(TO)}$	Overload threshold energy	V_{DD} = 13 V; V_{IS} = 5 V	-	0.4	-	J
$t_{d\ sc}$	Response time	V_{DD} = 13 V; V_{IS} = 5 V	-	0.8	-	ms
$I_{D(SC)}$	Drain current[3]	V_{DD} = 13 V; V_{IS} = 5 V	-	45	-	A
$I_{DM(SC)}$	Peak drain current[4]	V_{IS} = 5 V; V_{DD} = 13 V	-	105	-	A
	Over temperature protection					
$T_{j(TO)}$	Threshold junction temperature	V_{IS} = 5 V; from $I_D \ge 1$ A[5]	150	-	-	˚C

TRANSFER CHARACTERISTIC

T_{mb} = 25 ˚C

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	V_{DS} = 10 V; I_{DM} = 13 A $t_p \le 300$ µs; $\delta \le 0.01$	10	16	-	S

1 Continuous input voltage. The specified pulse width is for the drain current.

2 Refer to OVERLOAD PROTECTION LIMITING VALUES.

3 Continuous drain-source supply voltage. Pulsed input voltage.

4 Continuous input voltage. Momentary short circuit load connection. (The higher peak current is due to the effect of capacitance Cgd).

5 The over temperature protection feature requires a minimum on-state drain source voltage for correct operation. The specified minimum I_D ensures this condition.

INPUT CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified. The supply for the logic and overload protection is taken from the input.

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
$V_{IS(TO)}$	Input threshold voltage	V_{DS} = 5 V; I_D = 1 mA		1.0	1.5	2.0	V
I_{IS}	Input supply current	normal operation;	V_{IS} = 5 V	100	200	350	µA
			V_{IS} = 4 V	-	160	270	µA
V_{ISR}	Protection reset voltage[1]		T_j = 25 ˚C	2.0	2.6	3.5	V
			T_j = 150 ˚C	1.0	-	-	
I_{ISL}	Input supply current	protection latched;	V_{IS} = 5 V	-	330	650	µA
			V_{IS} = 3.5 V	-	240	430	µA
$V_{(BR)IS}$	Input breakdown voltage	I_I = 10 mA		6	-	-	V
R_{IG}	Input series resistance		T_j = 25 ˚C	-	33	-	kΩ
	to gate of power MOSFET		T_j = 150 ˚C	-	50	-	kΩ

SWITCHING CHARACTERISTICS

T_{mb} = 25 ˚C. R_I = 50 Ω . Refer to waveform figure and test circuit.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$t_{d\ on}$	Turn-on delay time	V_{DD} = 13 V; V_{IS} = 5 V	-	17	-	µs
t_r	Rise time	resistive load R_L = 2.1 Ω	-	75	-	µs
$t_{d\ off}$	Turn-off delay time	V_{DD} = 13 V; V_{IS} = 0 V	-	60	-	µs
t_f	Fall time	resistive load R_L = 2.1 Ω	-	70	-	µs

REVERSE DIODE LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_S	Continuous forward current	$T_{mb} \leq$ 25 ˚C; V_{IS} = 0 V	-	26	A

REVERSE DIODE CHARACTERISTICS

T_{mb} = 25 ˚C

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{SDO}	Forward voltage	I_S = 26 A; V_{IS} = 0 V; t_p = 300 µs	-	1.0	1.5	V
t_{rr}	Reverse recovery time	not applicable[2]	-	-	-	-

1 The input voltage below which the overload protection circuits will be reset.

2 The reverse diode of this type is not intended for applications requiring fast reverse recovery.

ENVELOPE CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
L_d	Internal drain inductance	Measured from contact screw on tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

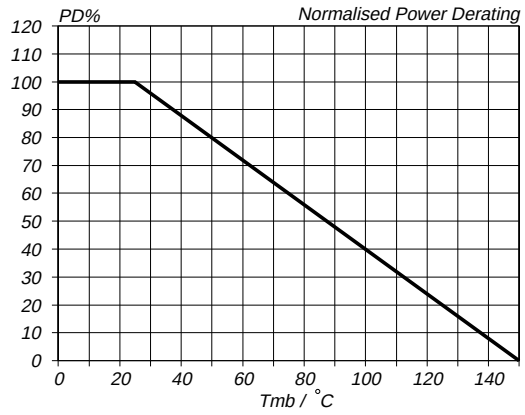


Fig.2. Normalised power dissipation.
$P_D\% = 100 \cdot P_D/P_D(25\ ^\circ C) = f(T_{mb})$

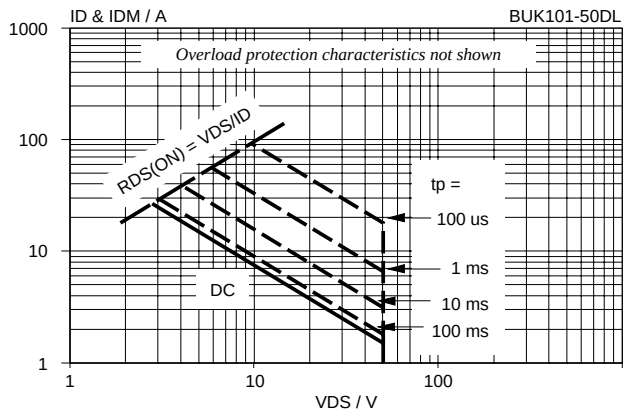


Fig.4. Safe operating area. $T_{mb} = 25\ ^\circ C$
I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

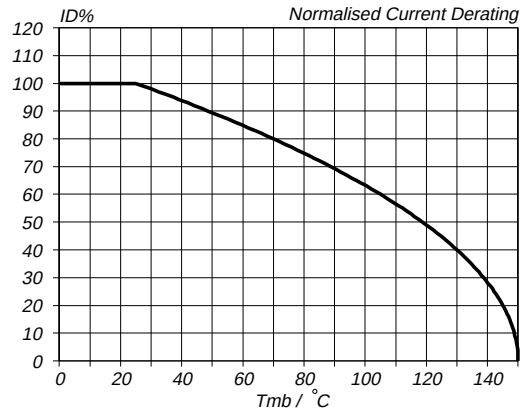


Fig.3. Normalised continuous drain current.
$I_D\% = 100 \cdot I_D/I_D(25\ ^\circ C) = f(T_{mb})$; conditions: $V_{IS} = 5$ V

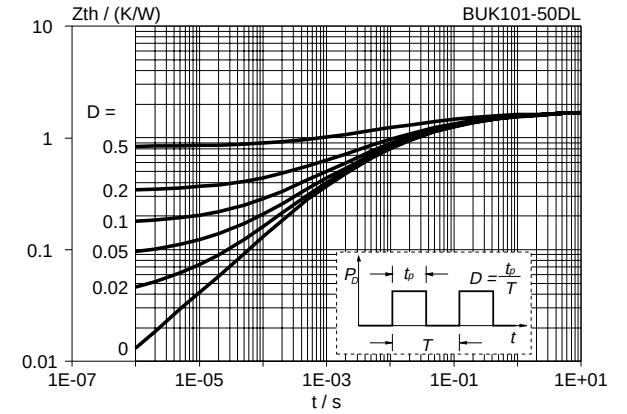


Fig.5. Transient thermal impedance.
$Z_{th\ j\text{-}mb} = f(t)$; parameter $D = t_p/T$

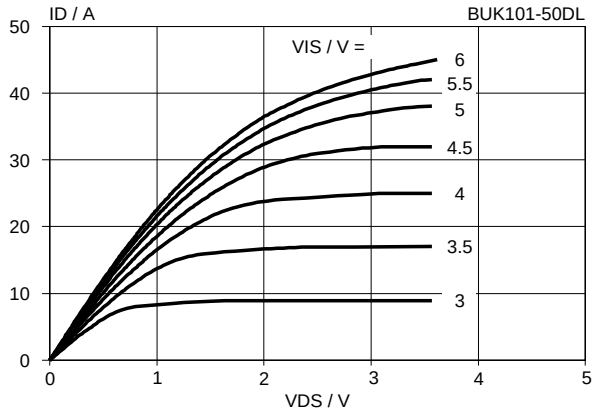


Fig.6. Typical on-state characteristics, T_j = 25 ˚C. ID = f(V_{DS}); parameter V_{IS}; t_p = 2 ms

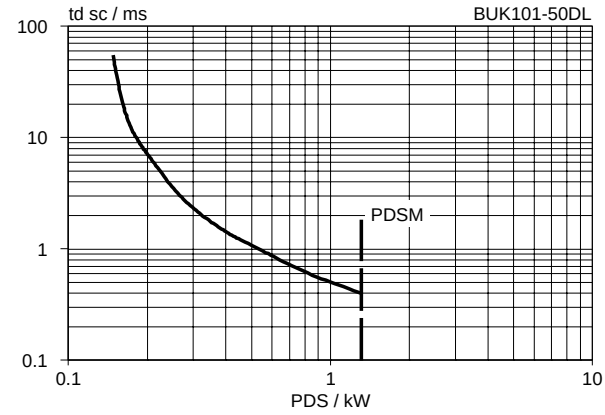


Fig.9. Typical overload protection characteristics. $t_{d\,sc}$ = f(P_{DS}); conditions: $V_{IS} \geq$ 4 V; T_j = 25 ˚C.

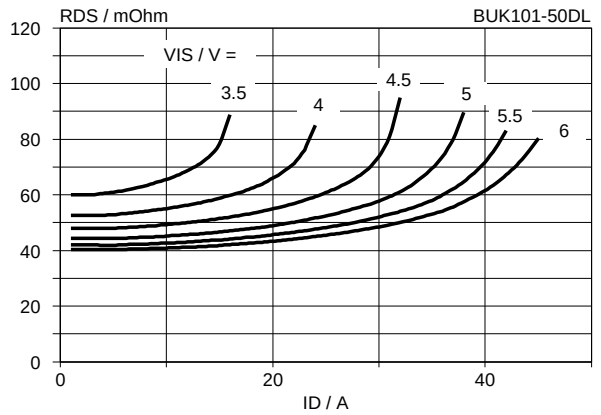


Fig.7. Typical on-state resistance, T_j = 25 ˚C. $R_{DS(ON)}$ = f(I_D); parameter V_{IS}; t_p = 2 ms

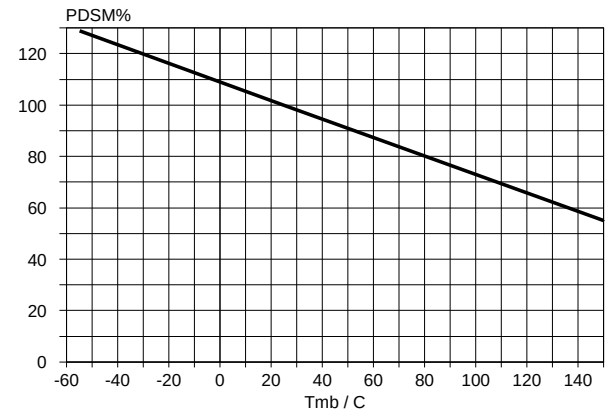


Fig.10. Normalised limiting overload dissipation. P_{DSM}% =100·P_{DSM}/P_{DSM}(25 ˚C) = f(T_{mb})

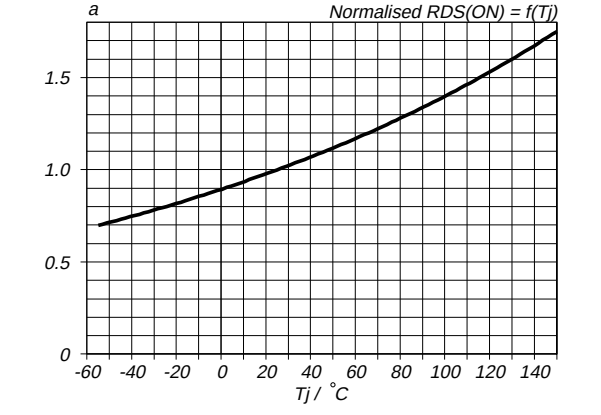


Fig.8. Normalised drain-source on-state resistance. a = $R_{DS(ON)}$/$R_{DS(ON)}$25 ˚C = f(T_j); I_D = 13 A; V_{IS} = 5 V

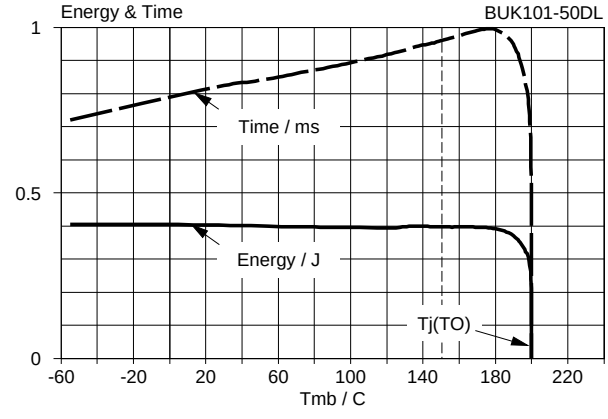


Fig.11. Typical overload protection characteristics. Conditions: V_{DD} = 13 V; V_{IS} = 5 V; SC load = 30 mΩ

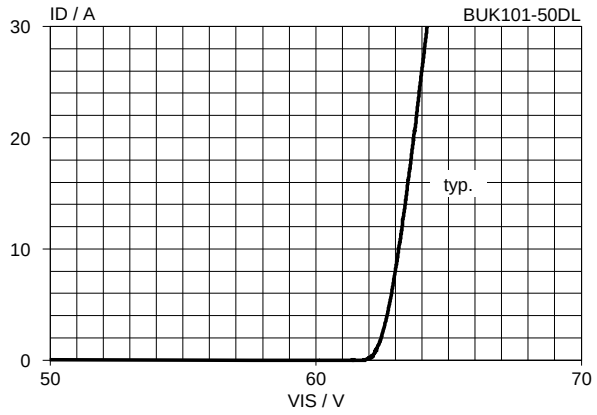


Fig.12. Typical clamping characteristics, 25 ˚C. $I_D = f(V_{DS})$; conditions: $V_{IS} = 0$ V; $t_p \leq 50$ µs

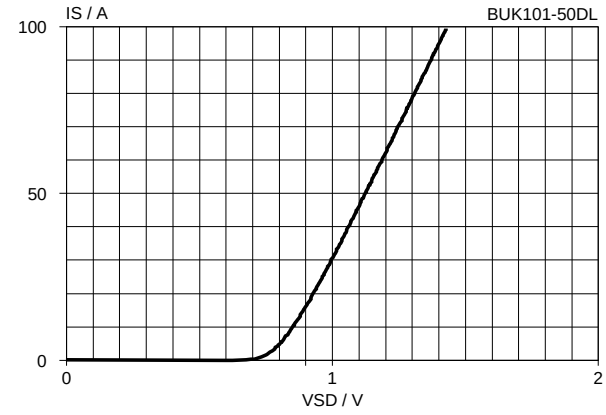


Fig.15. Typical reverse diode current, $T_j = 25$ ˚C. $I_S = f(V_{SDS})$; conditions: $V_{IS} = 0$ V

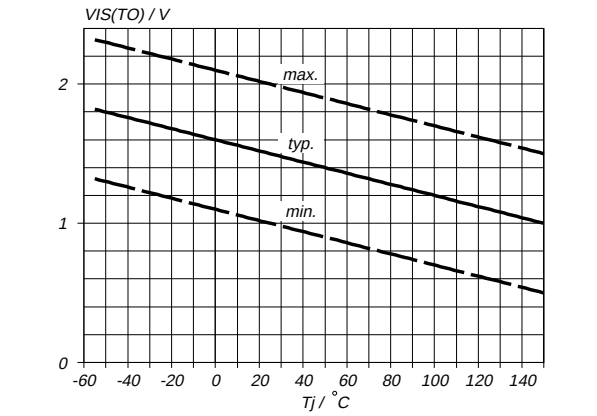


Fig.13. Input threshold voltage. $V_{IS(TO)} = f(T_j)$; conditions: $I_D = 1$ mA; $V_{DS} = 5$ V

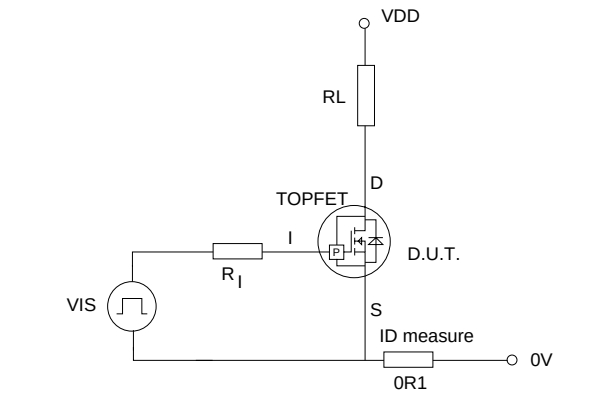


Fig.16. Test circuit for resistive load switching times.

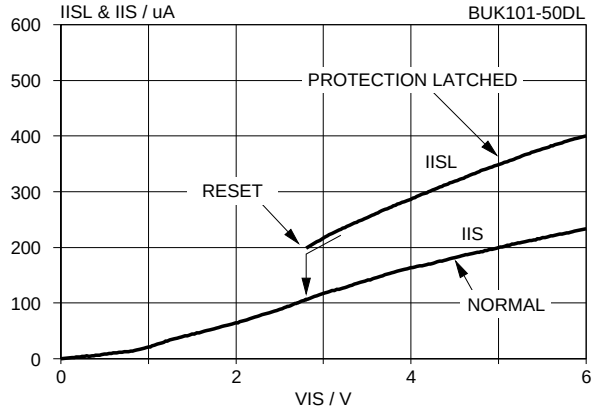


Fig.14. Typical DC input characteristics, $T_j = 25$ ˚C. I_{ISL} & $I_{IS} = f(V_{IS})$; protection latched & normal operation

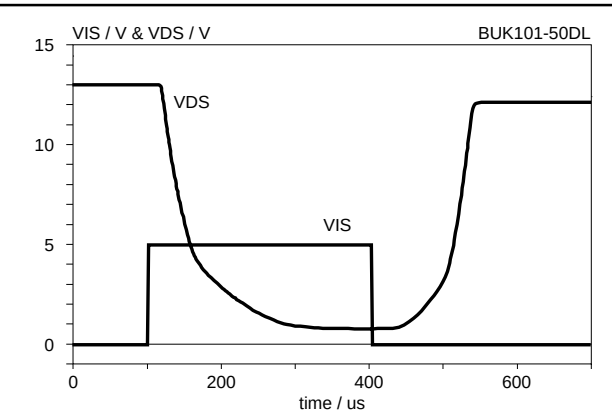


Fig.17. Typical switching waveforms, resistive load. $V_{DD} = 13$ V; $R_L = 2.1$ Ω; $R_I = 50$ Ω, $T_j = 25$ ˚C.

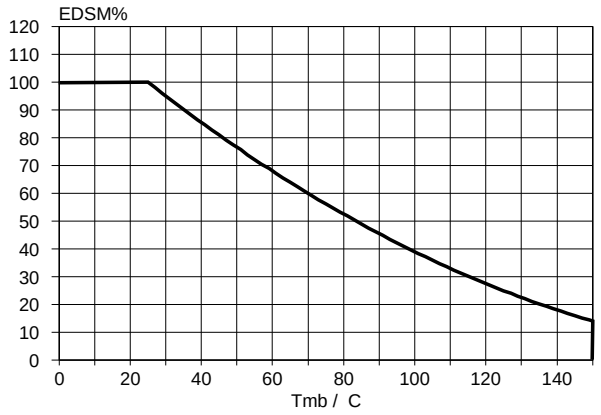


Fig.18. Normalised clamping energy rating.
E_{DSM}% = f(T_{mb}); conditions: I_D = 26 A; V_{IS} = 5 V

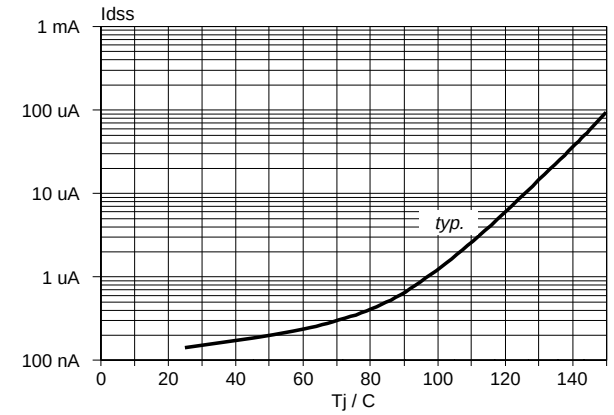


Fig.20. Typical off-state leakage current.
I_{DSS} = f(T_j); Conditions: V_{DS} = 40 V; I_{IS} = 0 V.

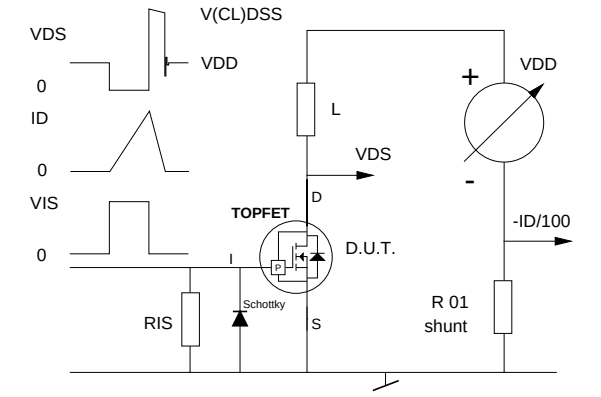


Fig.19. Clamping energy test circuit, R_{IS} = 50 Ω.
$$E_{DSM} = 0.5 \cdot L I_D^2 \cdot V_{(CL)DSS}/(V_{(CL)DSS} - V_{DD})$$

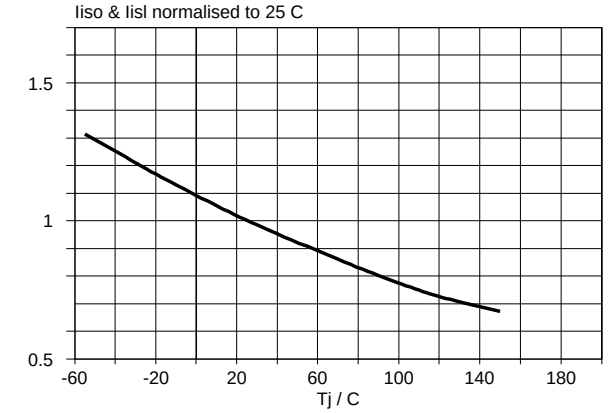


Fig.21. Normalised input currents (normal & latched).
$I_{ISO}/I_{ISO}25^{\circ}C$ & $I_{ISL}/I_{ISL}25^{\circ}C$ = f(T_j); V_{IS} = 5 V

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

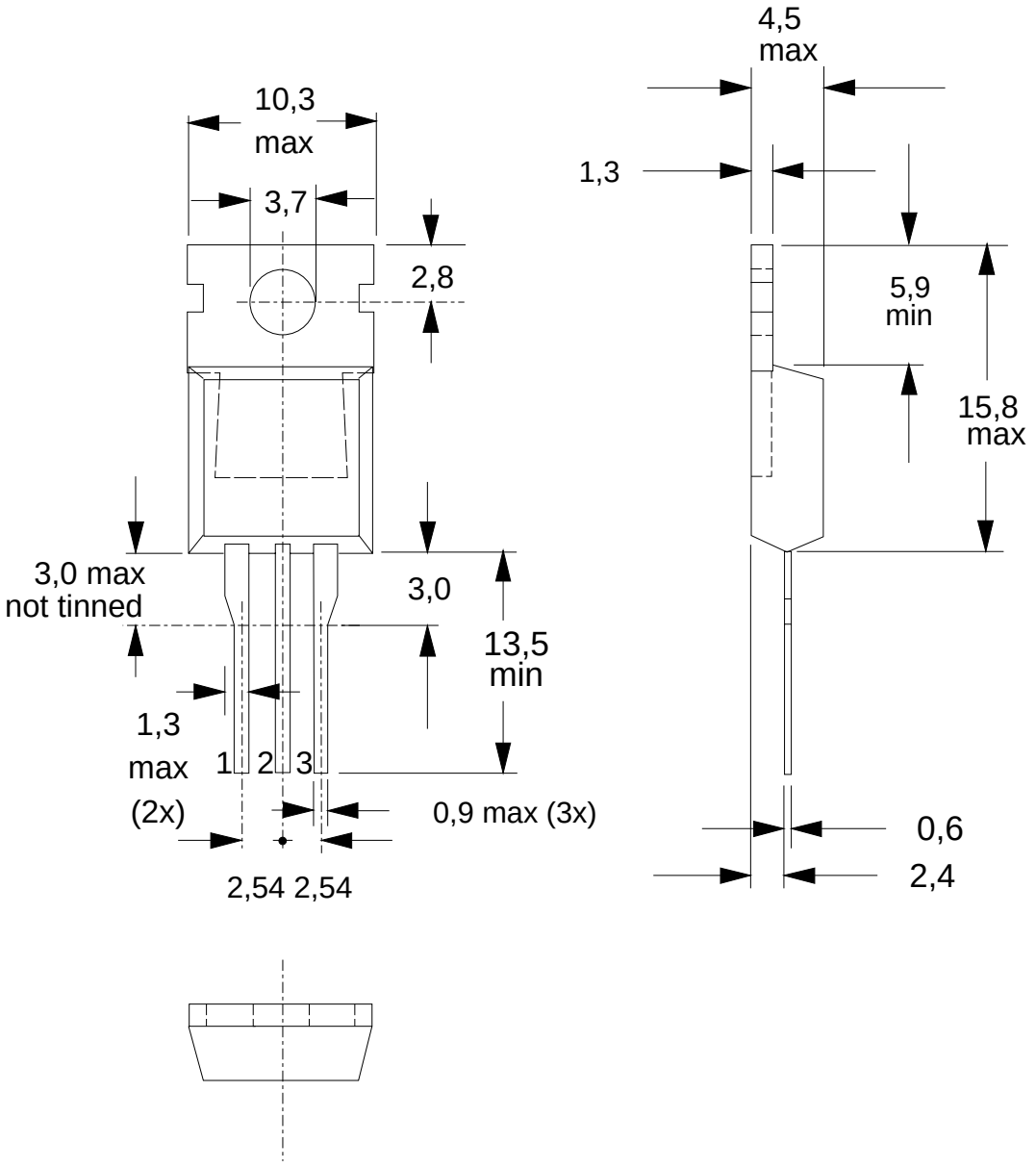


Fig.22. TO220AB; pin 2 connected to mounting base.

Notes
1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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